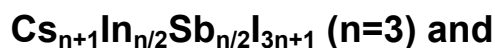


**Supplementary Information for “Promising photovoltaic and
solid-state-lighting materials: two-dimensional Ruddlesden-
Popper type lead-free halide double perovskites**



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Table S1 Values of the parameter *CUT* (in atomic units) and *l* together with the detailed half-ionized orbitals for M^+ , M^{3+} and X^- in our GGA-1/2 calculations are listed. Our *CUT* values for X^- are slightly smaller than those of ref. a-c (3.12, 3.34 and 3.76 for Cl^- , Br^- and I^-). This is because the anion *CUT* value usually has a small dependence on the chemical environment, as pointed out by Ferreira *et al.*^d

Atom	<i>CUT</i>	<i>l</i>	Half-ionized orbital	Atom	<i>CUT</i>	<i>l</i>	Half-ionized orbital
In^+	2.6	100	d	Sb^{3+}	2.8	90	d
Cu^+	2.8	100	d	Cl^-	2.9	100	p
Ag^+	3.1	100	d	Br^-	3.1	100	p
Au^+	3.0	100	d	I^-	3.4	100	p
Bi^{3+}	2.7	90	d				

^a J. Jiang, C. K. Onwudinanti, R. A. Hatton, P. A. Bobbert and S. Tao, *J. Phys. Chem. C*, 2018, **122**, 17660.

^b K. P. Marshall, S. Tao, M. Walker, D. S. Cook, J. Lloyd-Hughes, S. Varagnolo, A. Wijesekara, D. Walker, R. I. Walton and R. A. Hatton, *Mater. Chem. Front.*, 2018, **2**, 1515.

^c S. X. Tao, X. Cao and P. A. Bobbert, *Sci. Rep.*, 2017, **7**, 14386.

^d L. G. Ferreira, M. Marques and L. K. Teles, *Phys. Rev. B: Condens. Matter Mater. Phys.*, 2008, **78**, 125116.

Table S2 The dependence of the GGA-1/2 bandgap on the half-ionized orbitals of metal atoms in $\text{Cs}_2\text{In}_{1/2}\text{Sb}_{1/2}\text{I}_4$ and $\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{Cl}_4$, in which the half ionization of the p -orbital in I and Cl atoms is included. Compared with the accurate GW bandgap, we can easily find that the correction of d orbital for both M^+ and M^{3+} is necessary

Material	Half-ionized orbital	Bandgap (eV)
$\text{Cs}_2\text{In}_{1/2}\text{Sb}_{1/2}\text{I}_4$	In: \times Sb: \times	0.58
	In: p Sb: \times	0.62
	In: d Sb: \times	1.23
	In: d Sb: p	1.40
	In: d Sb: d	1.55, 1.55(GW)
$\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{Cl}_4$	Cu: \times Bi: \times	2.34
	Cu: p Bi: \times	2.80
	Cu: d Bi: \times	3.58
	Cu: d Bi: p	3.64
	Cu: d Bi: d	3.82, 3.82(GW)

Table S3 Fully optimized lattice parameter a (in unit of Å) in lead-free $n=1$ halide $\text{Cs}_2\text{M}^{+1/2}\text{M}^{3+1/2}\text{X}_4$ double perovskites. Some previous experimental results in bulk phase are also given

$\text{Cs}_2\text{M}^{+1/2}\text{M}^{3+1/2}$	X	a		$\text{Cs}_2\text{M}^{+1/2}\text{M}^{3+1/2}$	X	a
$\text{Cs}_2\text{In}_{1/2}\text{Bi}_{1/2}$	Cl	11.22		$\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}$	Cl	11.00
	Br	11.73			Br	11.50
	I	12.32			I	12.36
$\text{Cs}_2\text{In}_{1/2}\text{Sb}_{1/2}$	Cl	11.10		$\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}$	Cl	10.89
	Br	11.60			Br	11.37
	I	12.28			I	12.34
$\text{Cs}_2\text{Ag}_{1/2}\text{Bi}_{1/2}$	Cl	n=1 2D	10.98	$\text{Cs}_2\text{Au}_{1/2}\text{Bi}_{1/2}$	Cl	11.51
		bulk	10.78 ^(exp) ^a			
		$\text{Cs}_2\text{AgBiCl}_6$	10.85			
	Br	n=1 2D	11.53		Br	11.95
		bulk	11.27 ^(exp) ^b			
		$\text{Cs}_2\text{AgBiBr}_6$	11.30			
I	12.36		I	12.64		
$\text{Cs}_2\text{Ag}_{1/2}\text{Sb}_{1/2}$	Cl	10.87		$\text{Cs}_2\text{Au}_{1/2}\text{Sb}_{1/2}$	Cl	11.39
	Br	11.41			Br	11.82
	I	12.24			I	12.42

^a E. T. McClure, M. R. Ball, W. Windl and P. M. Woodward, *Chem. Mater.*, 2016, **28**, 1348.

^bA. H. Slavney, T. Hu, A. M. Lindenberg and H. I. Karunadasa, *J. Am. Chem. Soc.*, 2016, **138**, 2138.

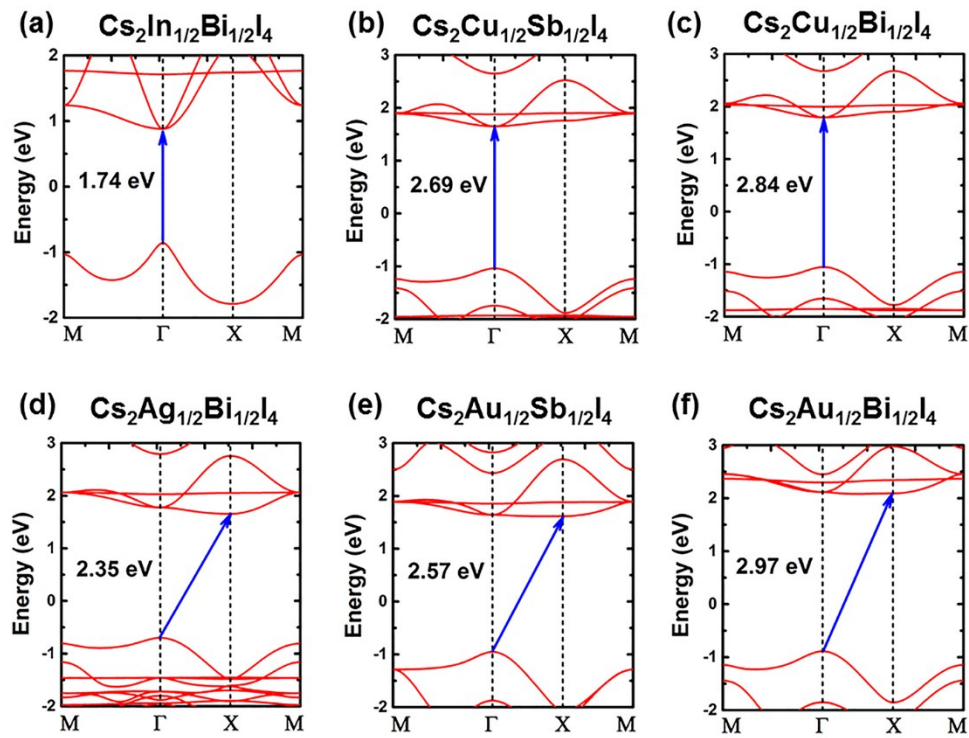


Figure S1 Energy band structures of $n=1$ lead-free halide double perovskites with direct bandgap (a) $\text{Cs}_2\text{In}_{1/2}\text{Bi}_{1/2}\text{I}_4$, (b) $\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{I}_4$ and (c) $\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{I}_4$, and indirect bandgap (d) $\text{Cs}_2\text{Ag}_{1/2}\text{Bi}_{1/2}\text{I}_4$, (e) $\text{Cs}_2\text{Au}_{1/2}\text{Sb}_{1/2}\text{I}_4$ and (f) $\text{Cs}_2\text{Au}_{1/2}\text{Bi}_{1/2}\text{I}_4$. Here, the band structures are derived from the GGA-PBE calculations, in which the underestimated bandgaps are modified according to GGA-1/2 calculations.

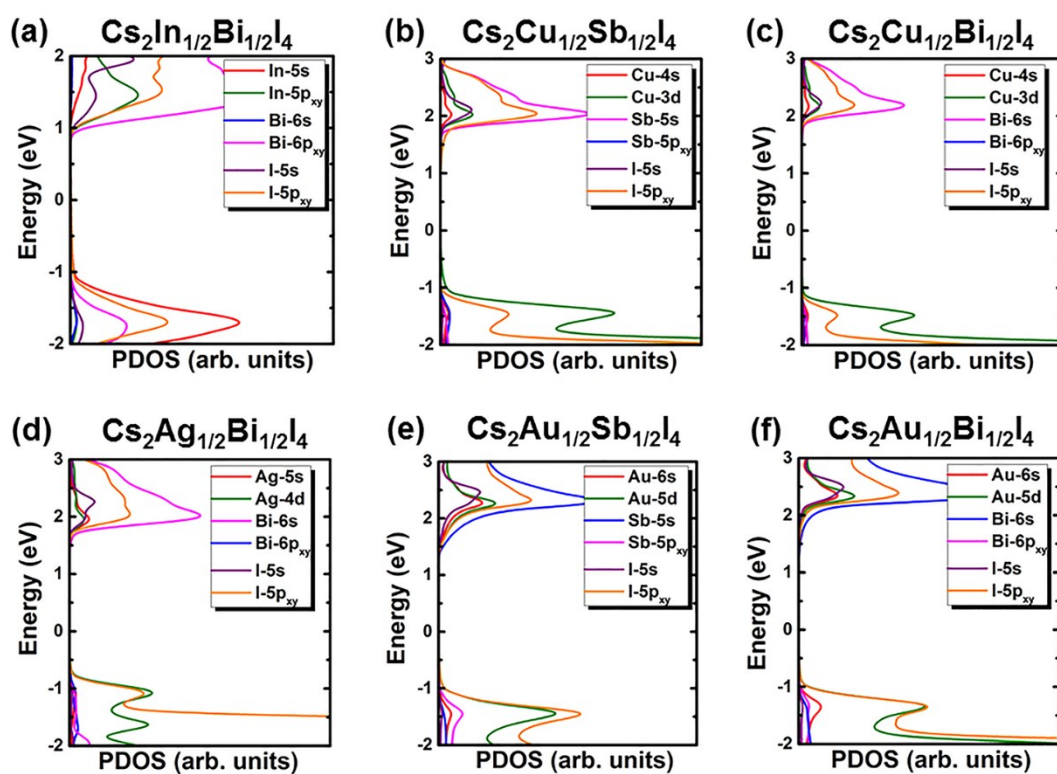


Figure S2 PDOSs of $n=1$ lead-free halide double perovskites with direct bandgap (a) $\text{Cs}_2\text{In}_{1/2}\text{Bi}_{1/2}\text{I}_4$, (b) $\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{I}_4$ and (c) $\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{I}_4$, and indirect bandgap (d) $\text{Cs}_2\text{Ag}_{1/2}\text{Bi}_{1/2}\text{I}_4$, (e) $\text{Cs}_2\text{Au}_{1/2}\text{Sb}_{1/2}\text{I}_4$ and (f) $\text{Cs}_2\text{Au}_{1/2}\text{Bi}_{1/2}\text{I}_4$.

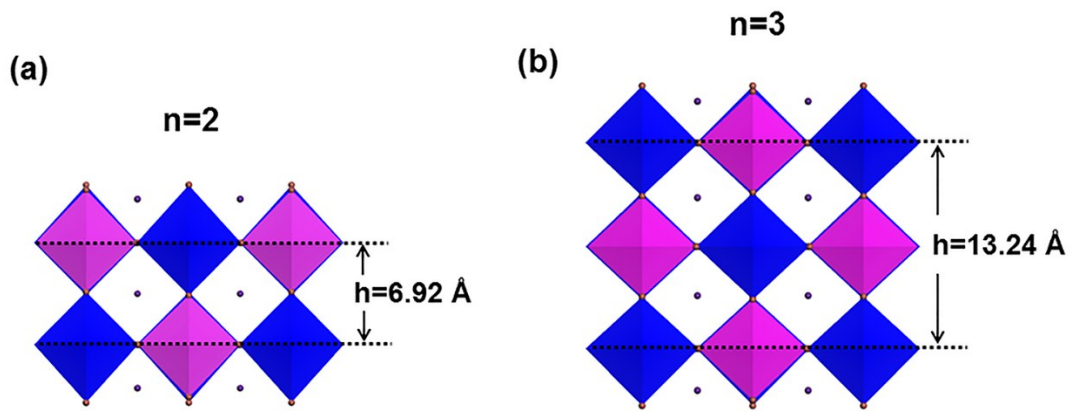


Figure S3 The 2D double perovskite crystal structures of (a) $n=2$ $\text{Cs}_3\text{InSbI}_7$ and (b) $n=3$ $\text{Cs}_4\text{In}_{3/2}\text{Sb}_{3/2}\text{I}_{10}$ with the vertical distance of $h=6.92$ and 13.24 \AA , respectively. Here, the stacking order of layered double perovskites, composed by the alternative M^+X (pink) and M^{3+}X (blue) octahedrons, is similar to their bulk counterparts.

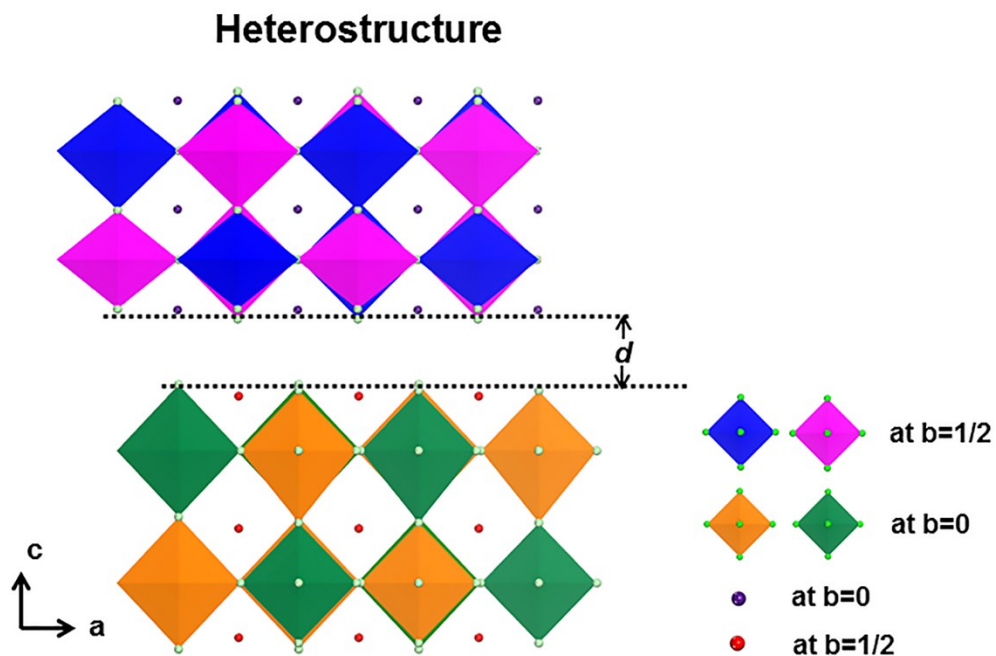


Figure S4 Schematic illustration of the crystal structure of 2D lead-free halide double perovskite heterostructure. The different perovskite layers in the heterostructure are directly stacked together with a shift of $b/2$ along the b -axis just as the bulk RP-type perovskite. A suitable strain exists to match the lattice constants of different layers. The d represents the interlayer distance between two different layers in the heterostructure.

Table S4 The interlayer distance d (Å) and lattice mismatch of all considered 2D RP-type lead-free halide double perovskite heterostructures

Material	Layer thickness	d	Lattice mismatch
CsInSbCl/CsCuBiCl	$n=1/m=1$	5.51	0.45%
	$n=2/m=1$	5.54	0.67%
	$n=1/m=2$	5.56	0.51%
	$n=2/m=2$	5.65	0.53%
	$n=3/m=1$	5.62	0.72%
CsInBiCl/CsCuBiCl	$n=1/m=1$	5.58	0.98%
CsInSbCl/CsAgBiCl	$n=1/m=1$	5.59	0.54%
CsInBiCl/CsCuSbCl	$n=1/m=1$	5.57	1.47%
CsAgSbBr/CsCuSbCl	$n=1/m=1$	5.64	2.27%
CsAgSbBr/CsCuSbBr	$n=1/m=1$	5.78	0.17%
CsAgSbI/CsCuSbI	$n=1/m=1$	5.69	0.41%

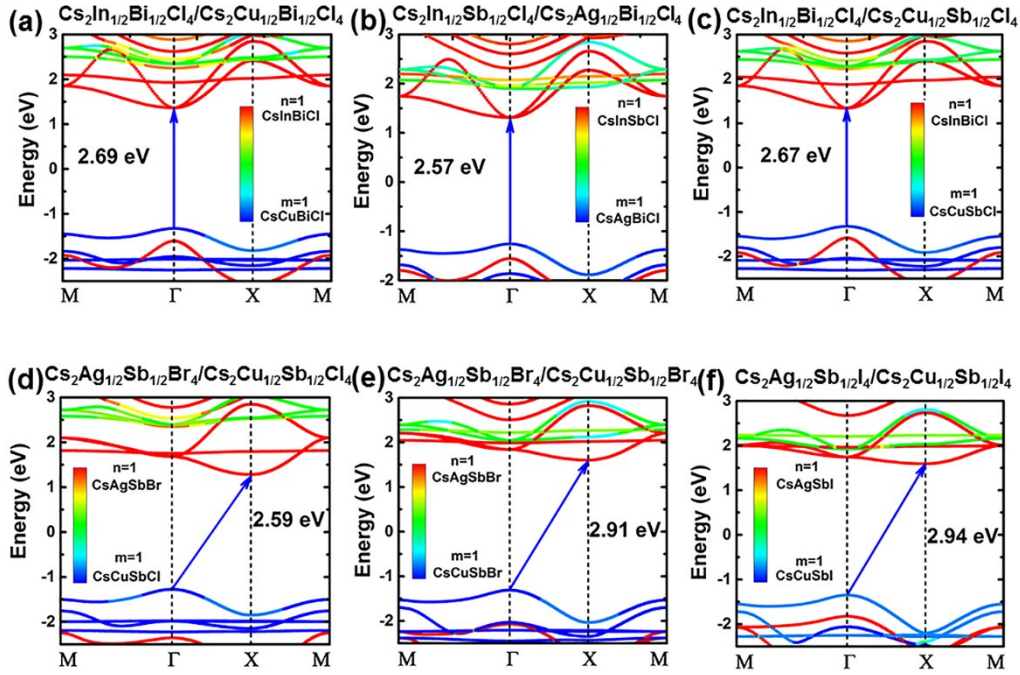


Figure S5 The weighted energy band structures of $n=1/m=1$ lead-free halide double perovskite heterostructures with type-II band alignment can be classified into two types, *i.e.*, direct bandgap (a) $\text{Cs}_2\text{In}_{1/2}\text{Bi}_{1/2}\text{Cl}_4/\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{Cl}_4$, (b) $\text{Cs}_2\text{In}_{1/2}\text{Sb}_{1/2}\text{Cl}_4/\text{Cs}_2\text{Ag}_{1/2}\text{Bi}_{1/2}\text{Cl}_4$ and (c) $\text{Cs}_2\text{In}_{1/2}\text{Bi}_{1/2}\text{Cl}_4/\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{Cl}_4$ and indirect bandgap (d) $\text{Cs}_2\text{Ag}_{1/2}\text{Sb}_{1/2}\text{Br}_4/\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{Cl}_4$, (e) $\text{Cs}_2\text{Ag}_{1/2}\text{Sb}_{1/2}\text{Br}_4/\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{Br}_4$ and (f) $\text{Cs}_2\text{Ag}_{1/2}\text{Sb}_{1/2}\text{I}_4/\text{Cs}_2\text{Cu}_{1/2}\text{Sb}_{1/2}\text{I}_4$. Here, the band structures are derived from the GGA-PBE calculations, in which the underestimated bandgaps are modified according to GGA-1/2 calculations.

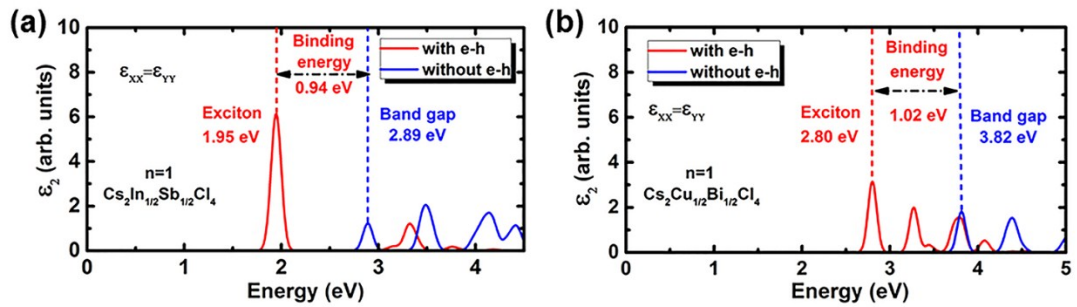


Figure S6 The calculated imaginary parts ϵ_2 of dielectric function for freestanding $n=1$ (a) $\text{Cs}_2\text{In}_{1/2}\text{Sb}_{1/2}\text{Cl}_4$ and (b) $\text{Cs}_2\text{Cu}_{1/2}\text{Bi}_{1/2}\text{Cl}_4$.

Table S5 The carrier effective mass m^* (m_0) and the predicted carrier mobility μ ($\text{cm}^2\text{V}^{-1}\text{s}^{-1}$) in 2D lead-free $n=1$ halide double perovskite $\text{Cs}_2\text{M}^{+} \text{1/2M}^{3+} \text{1/2X}^{-4}$ and their $n=1/m=1$ heterostructures

Material	X	m_h^*	m_e^*	μ_h	μ_e	Material	X	m_h^*	m_e^*	μ_h	μ_e
MAPbI ₃	I	0.30	1.14	0.24		MASnI ₃	I	0.22	1.10	0.18	
Cs ₂ In _{1/2} Bi _{1/2}	Cl	0.52	1.09	40	25	Cs ₂ Cu _{1/2} Bi _{1/2}	Cl	0.85	0.90	26	10
	Br	0.42	0.94	254	145		Br	0.81	0.88	76	58
	I	0.21	0.64	590	145		I	0.75	0.84	110	96
Cs ₂ In _{1/2} Sb _{1/2}	Cl	0.45	1.08	86	72	Cs ₂ Cu _{1/2} Sb _{1/2}	Cl	0.80	0.84	150	121
	Br	0.33	0.93	321	198		Br	0.74	0.82	230	165
	I	0.18	0.70	655	309		I	0.62	0.80	311	196
Cs ₂ Ag _{1/2} Bi _{1/2}	Cl	0.85	1.02	30	11	Cs ₂ Au _{1/2} Bi _{1/2}	Cl	0.96	1.05	40	14
	Br	0.74	0.98	101	50		Br	0.85	0.94	90	41
	I	0.66	0.93	210	121		I	0.76	0.86	160	100
Cs ₂ Ag _{1/2} Sb _{1/2}	Cl	0.83	1.06	50	30	Cs ₂ Au _{1/2} Sb _{1/2}	Cl	0.90	1.02	92	55
	Br	0.71	1.02	111	41		Br	0.81	0.89	160	117
	I	0.60	0.97	200	107		I	0.75	0.81	234	160
Cs ₂ In _{1/2} Sb _{1/2} Cl ₄ / Cs ₂ Cu _{1/2} Bi _{1/2} Cl ₄		0.80	0.87	70	165	Cs ₂ Ag _{1/2} Sb _{1/2} Br ₄ / Cs ₂ Cu _{1/2} Sb _{1/2} Cl ₄		0.76	0.72	330	90
Cs ₂ In _{1/2} Bi _{1/2} Cl ₄ / Cs ₂ Cu _{1/2} Bi _{1/2} Cl ₄		0.81	0.90	50	65	Cs ₂ Ag _{1/2} Sb _{1/2} Br ₄ / Cs ₂ Cu _{1/2} Sb _{1/2} Br ₄		0.74	0.81	395	110
Cs ₂ In _{1/2} Sb _{1/2} Cl ₄ / Cs ₂ Ag _{1/2} Bi _{1/2} Cl ₄		0.85	0.42	50	122	Cs ₂ Ag _{1/2} Sb _{1/2} I ₄ / Cs ₂ Cu _{1/2} Sb _{1/2} I ₄		0.56	0.89	598	224
Cs ₂ In _{1/2} Bi _{1/2} Cl ₄ / Cs ₂ Cu _{1/2} Sb _{1/2} Cl ₄		0.80	0.42	74	70						